Abstract Submitted
for the MAR17 Meeting of
The American Physical Society

Growth of TiSe2 Thin Films Using Chemical Vapor Transport[1]
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[1]This work was supported as part of the CCDM, an Energy Frontier Research Center funded by the U.S. Department of Energy, Office of Science under Award DE-SC0012575.

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Date submitted: 11 Nov 2016 Electronic form version 1.4